

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max $T_C = +25^\circ C$
100V	23m Ω @ $V_{GS} = 10V$	41.2A
	30m Ω @ $V_{GS} = 6V$	36.1A

Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Applications

- Power Management Functions
- DC-DC Converters
- Backlighting

Features

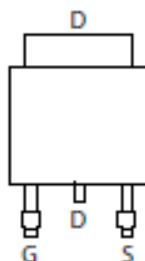
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low $R_{DS(ON)}$ – Minimizes Power Losses
- Low Q_G – Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

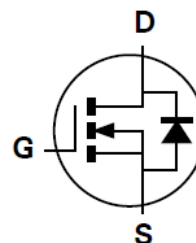
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.33 grams (Approximate)



Top View



Pin Out Top View



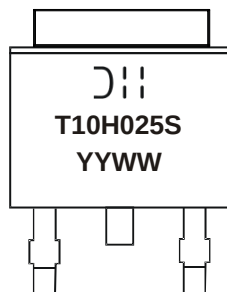
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT10H025SK3-13	TO252 (DPAK)	2,500/Tape & Reel

- Notes:
- EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 - See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



DII = Manufacturer's Marking
 T10H025S = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 18 = 2018)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	100	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V	I _D	41.2 32.9	A
		T _C = +25°C T _C = +70°C	
Pulsed Drain Current (10μs Pulse, T _C =+25°C, Package Limited)	I _{DM}	160	A
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	45	A
Pulsed Body Diode Forward Current (10μs Pulse, T _C =+25°C, Package Limited)	I _{SM}	160	A
Avalanche Current, L = 0.1mH (Note 8)	I _{AS}	7.5	A
Avalanche Energy, L = 0.1mH (Note 8)	E _{AS}	2.8	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	1.4	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	81	°C/W
Total Power Dissipation (Note 6)	P _D	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	46	°C/W
Thermal Resistance, Junction to Case	R _{θJC}	2.1	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 80V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	2	—	4	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	17.8	23	mΩ	V _{GS} = 10V, I _D = 20A
		—	22.9	30		V _{GS} = 6V, I _D = 20A
Diode Forward Voltage	V _{SD}	—	0.9	1.3	V	V _{GS} = 0V, I _S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	1544	—	pF	V _{DS} = 50V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	250	—		
Reverse Transfer Capacitance	C _{rss}	—	20.4	—		
Gate Resistance	R _g	—	1.26	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	21.4	—	nC	V _{DD} = 50V, I _D = 20A
Total Gate Charge (V _{GS} = 6V)	Q _g	—	13.4	—		
Gate-Source Charge	Q _{gs}	—	4.6	—		
Gate-Drain Charge	Q _{gd}	—	6.0	—		
Turn-On Delay Time	t _{D(ON)}	—	8.2	—	ns	V _{DD} = 50V, V _{GS} = 10V, I _D = 20A, R _g = 11Ω
Turn-On Rise Time	t _r	—	11.2	—		
Turn-Off Delay Time	t _{D(OFF)}	—	27.5	—		
Turn-Off Fall Time	t _f	—	13.7	—		
Reverse Recovery Time	t _{RR}	—	37.5	—	ns	I _F = 20A, di/dt = 100A/μs
Reverse Recovery Charge	Q _{RR}	—	50.9	—	nC	

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
 6. Thermal resistance from junction to soldering point (on the exposed drain pad).
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.

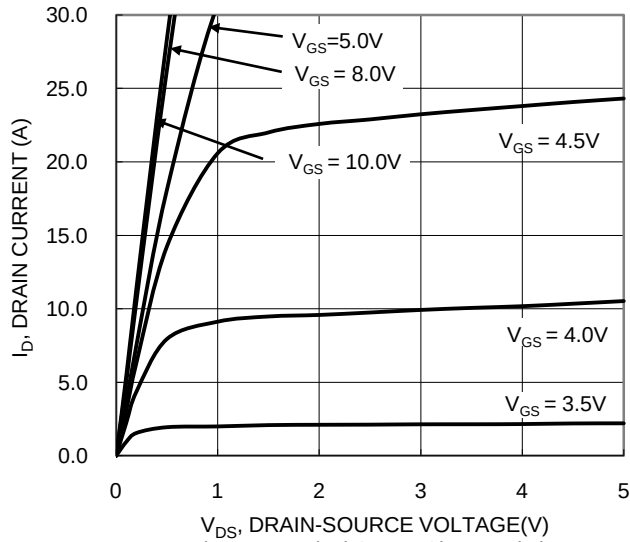


Figure 1. Typical Output Characteristic

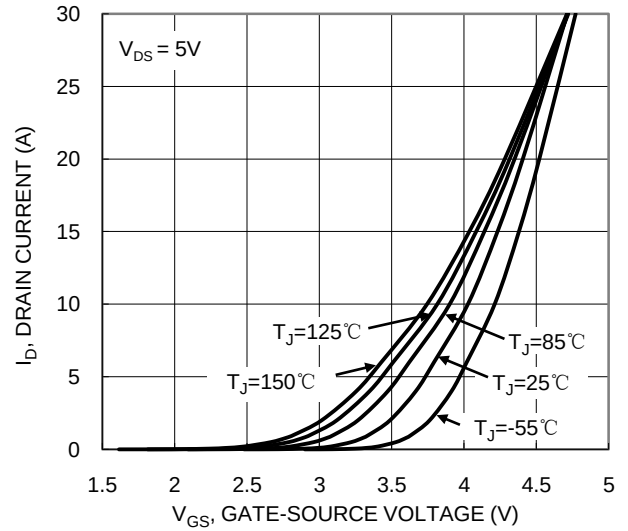


Figure 2. Typical Transfer Characteristic

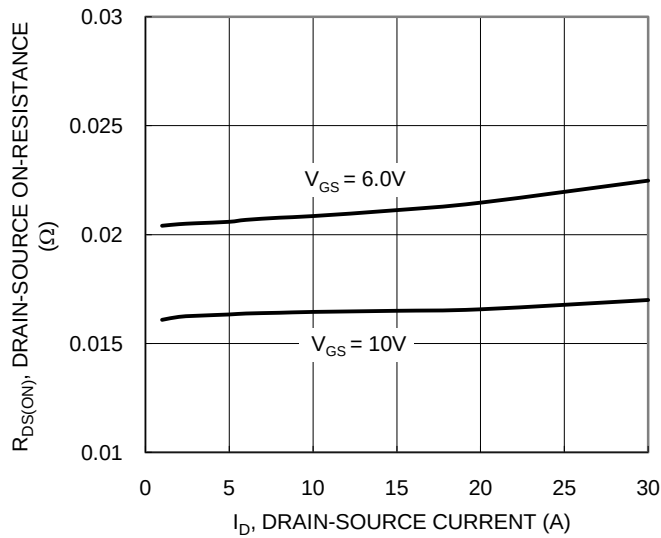


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

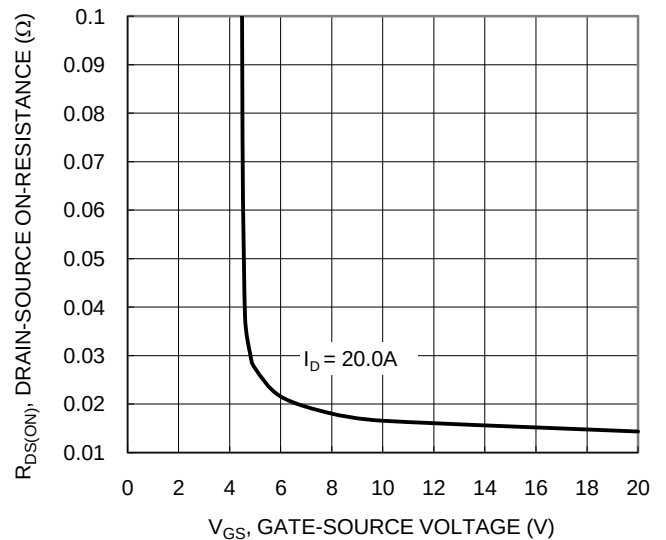


Figure 4. Typical Transfer Characteristic

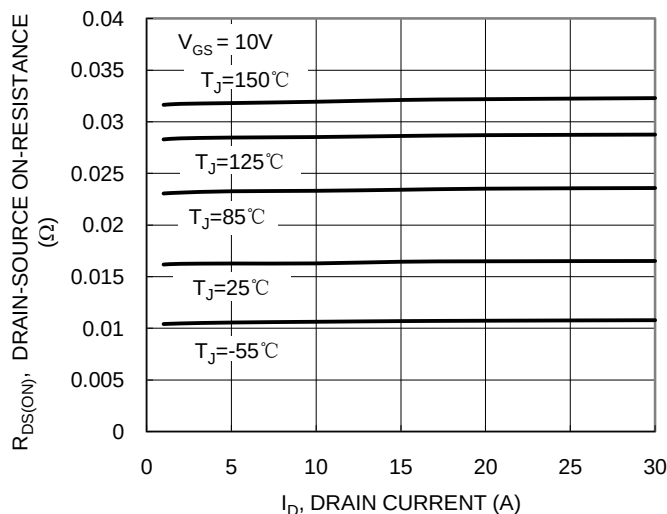


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

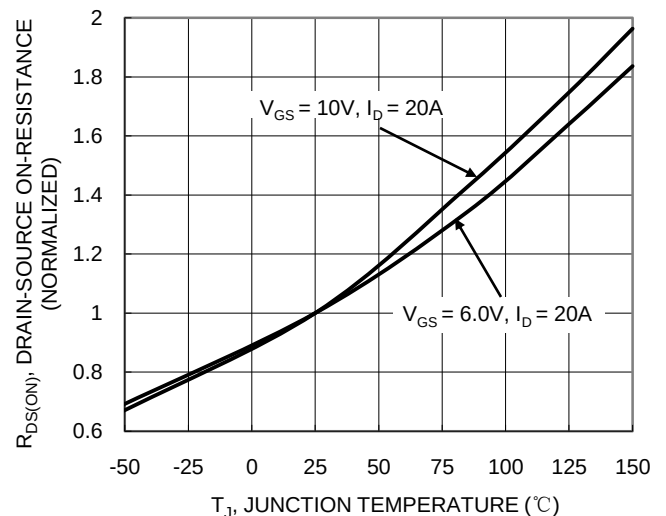
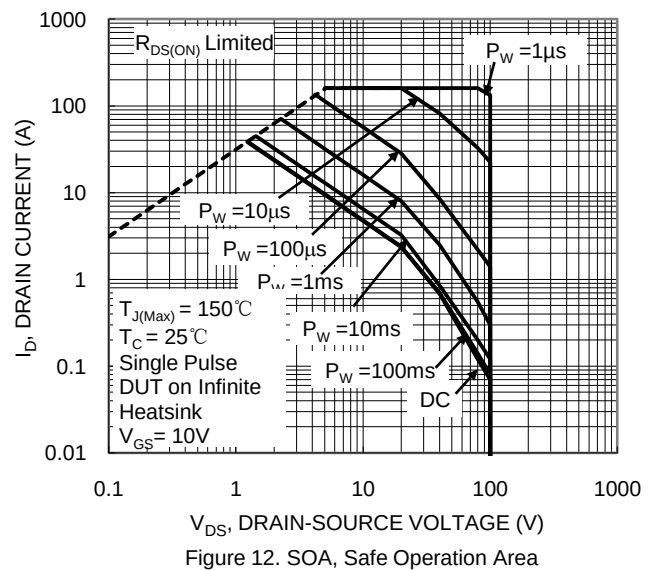
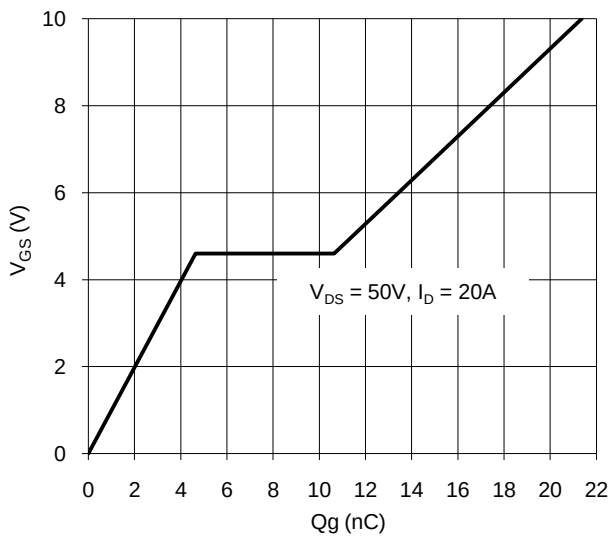
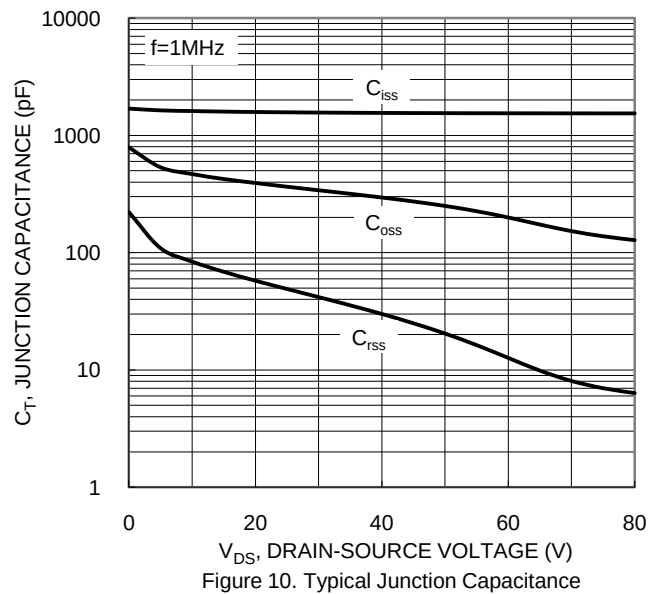
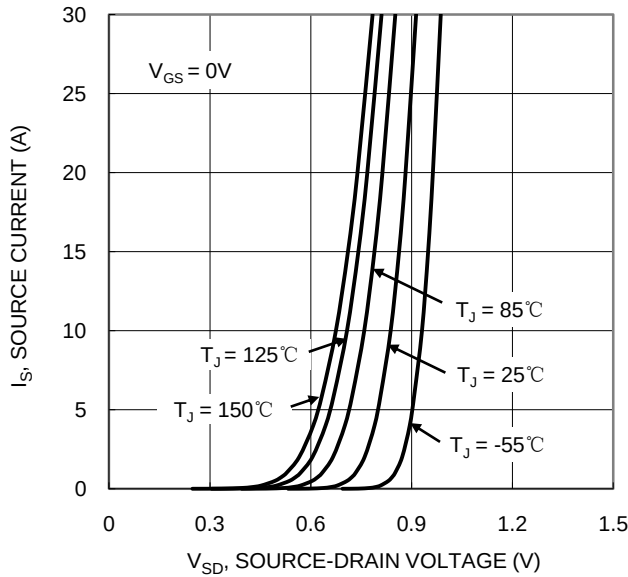
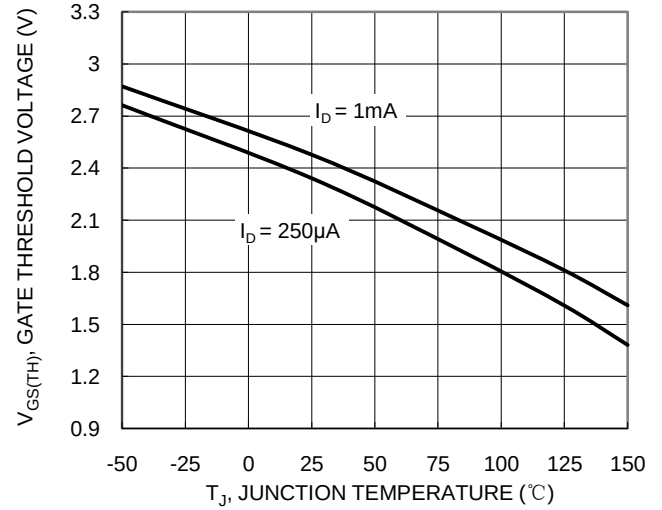
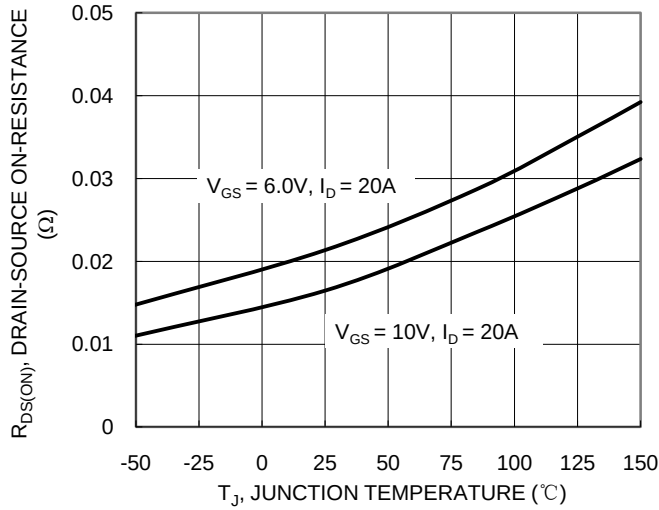


Figure 6. On-Resistance Variation with Junction Temperature



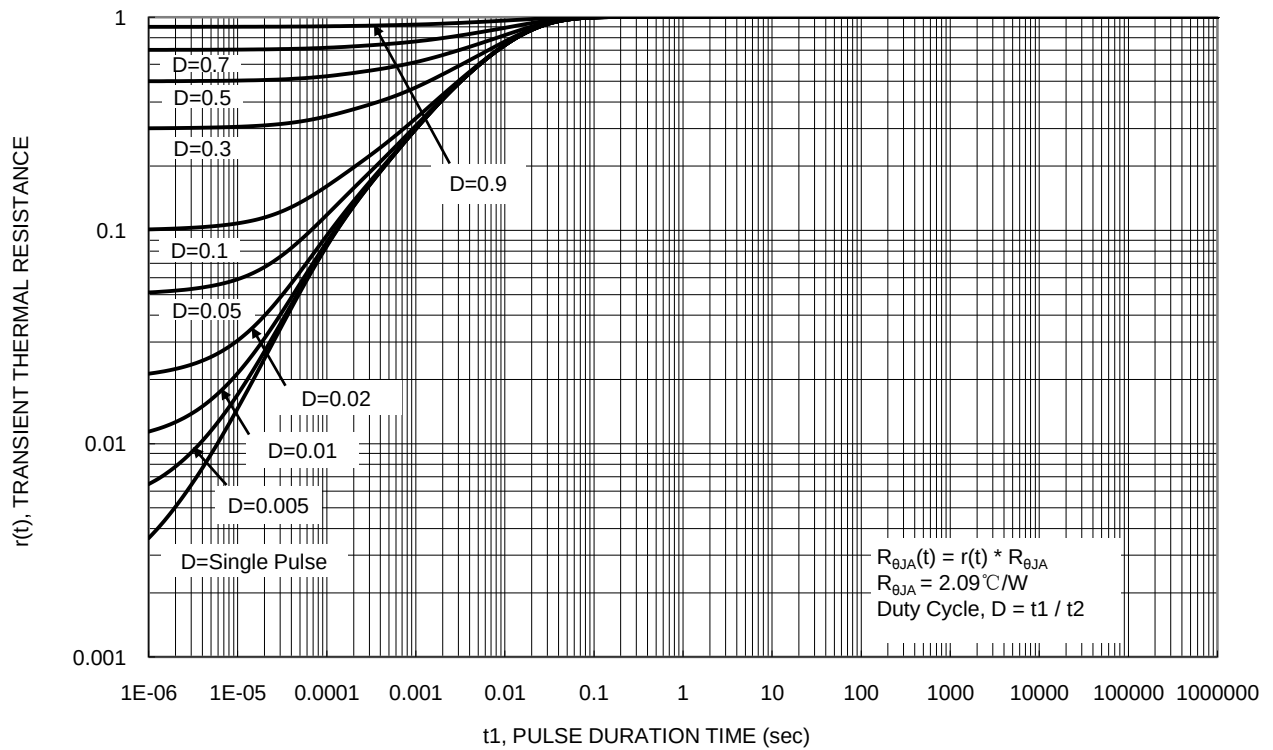
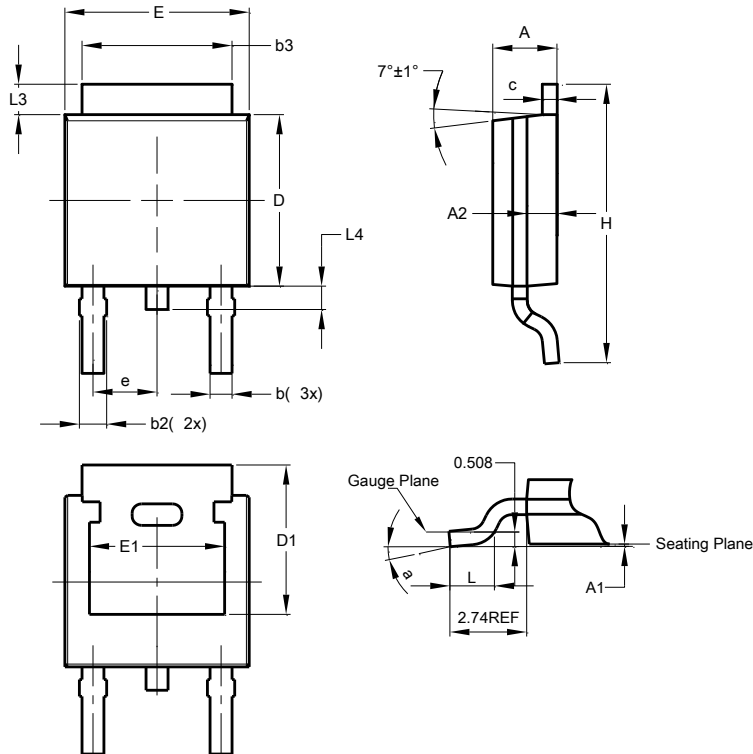


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)

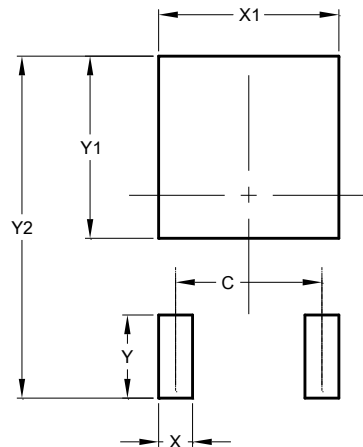


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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